CALL FOR PAPERS
FINAL ANNOUNCEMENT

2000 INTERNATIONAL CONFERENCE ON SOLID STATE DEVICES AND MATERIALS

Short Course: August 28, 2000
Conference: August 29-31, 2000

The 2000 International Conference on Solid State Devices and Materials (SSDM 2000) will be held from August 29 (Tuesday) through August 31 (Thursday), 2000 at the Sendai International Center, Sendai. Since 1969, the conference has provided good opportunity to discuss key aspects of solid state devices and materials. From the last conference, fifteen program sub-committees have been organized for covering circuit and system areas as well as device and material areas. In addition, half-day short courses are scheduled prior to the conference, which offer tutorial lectures on important topics.

Original and unpublished papers will be accepted after being reviewed by the Program Committee.

Several invited speakers will overview topics of current interest.

Advance Program will appear in July.

On-line information about SSDM 2000 is available on the World Wide Web at:
http://ssdm.bcasj.or.jp/

PLENARY SESSIONS

Plenary Speakers:
J. F. Gibbons (Stanford Univ.)
R. Tummala (Georgia Inst. of Technology)
M. Kawachi (NTT)
D.J. Harrison(Univ. of Alberta)

SCOPE OF CONFERENCE

From the last conference, fifteen program sub-committees have been organized. This organization is intended to bring higher quality of paper selection and strengthening in specific technology areas. The scope of each subcommittee is listed below.

Core Areas

[1] Advanced Silicon Circuits and Systems (Chair, T. Shibata, Univ. of Tokyo)

Papers bridging the gap between the material/device technologies and system technologies for enhancing the total system performance are solicited in the following areas (but not limited): (1) New concept circuits, (2) Advanced architecture and systems, (3) Advanced digital/analog circuits and systems, (4) Functional devices and their circuit applications, (5) New materials for advanced circuits, (6) Neuromorphic systems, and (7) Imaging and image processing systems.

Invited Speakers:
W. Liu (North Carolina State Univ)
" Prospective of Implantable Microsystem Technology and Experience on the Artificial Vision System "
S. Shigematsu, H. Morimura, Y. Tanabe, K. Machida and H. Kyuragi (NTT)
" Fingerprint Identification System on a Single Chip Based on Advanced Circuit and Device Technologies"

[2] Advanced Silicon Devices and Device Physics (Chair, S. Kawamura, Fujitsu)

The scope of this subcommittee covers all aspects of advanced silicon devices, such as (1) Sub-0.1 um silicon CMOS devices including logic, memory and merged logic/memory, (2) New concepts, theories and breakthroughs in silicon-related devices, (3) Advanced silicon devices related to SiGe and other new materials, and (4) Physics for advanced devices including simulation and modeling.

Invited Speakers:
J. Hergenrother (Bell Labs. Lucent Technol.)
" The Vertical Replacement-Gate (VRG) MOSFET:A High-Performance Vertical MOSFET with Lithography-Independent Critical Dimensions "
S. Deleonibus (LETI)
" 20nm MOS Devices for the Birth of the 21st Century, the Era of Ultimate CMOS "

[3] Silicon Process / Materials Technologies (Chair, T. Kikkawa, Hiroshima Univ.)

The scope is to bring together new and/or advanced technologies for Si ULSI fabrication processes and materials. Papers are solicited in, but not limited to, the following areas: (1) New processes and materials for the breakthrough of Si ULSI fabrication, and (2) Improved processes and materials technologies for sub-0.18um devices.

Invited Speakers:
M. Bohr (Intel)
" Integrated Circuit Challenges, from Transistors to Packages "
J. Reid (Novellus Systems)
" Copper Electrochemical Deposition: Principles and Recent Progress"
N. Fukushima (Toshiba)
" TBD "

[4] High-Speed/High-Frequency Devices and Circuits (Chair, K. Honjo, NEC)

Papers are solicited in, but not limited to, the following areas: (1) Microwave and millimeter-wave devices and their circuit applications, (2) High speed devices and their integrated circuits, and (3) Characterizations and analyses for system and circuit applications.

Invited Speaker:
K. Washio (Hitachi)
" Self-Aligned SiGe HBT Technology for Optical-Fiber-Links and Millimeter-Wave Applications"

[5] Optoelectronic Devices (Chair, H. Ishikawa, Fujitsu Labs.)

The scope of this subcommittee covers all aspects of optoelectronics devices, such as (1) Laser diodes, LEDs, photo-detectors, optical amplifiers, modulators and switches, (2) Functional optical devices and monolithic integrations, and (3)

Epitaxial growth and wafer process of optoelectronic materials and devices.

Invited Speakers:
H. Ito (NTT)
" High-Speed Uni-Traveling-Carrier Photodiodes for Fiber-Optic Communications "
K. Tajima, S. Nakamura, Y. Ueno, J. Sasaki, T. Sugimoto, T. Kato, T. Shimoda, H. Hatakeyama, T. Tamanuki and T. Sasaki (NEC)
" Ultrafast Demultiplexing and Bit-Wise Logic Operation of Hybrid-Integrated Symmetric Mach-Zehnder All-Optical Switch "

[6] Compound Semiconductor Materials and Device Processes (Chair, Y. Horikoshi, Waseda Univ.)

Basic technology for III-V, II-VI and other compound semiconductors including the following areas (but not limited): (1) Growth and characterization, (2) Heterostructure and superlattices (3) Device processing and reliability.

Invited Speakers:
B. Bayraktaroglu (ANADIGICS)
" Modern Processing Technology for 6-inch GaAs Wafers "
S. Yamahata, M. Ida, K. Kurishima, H. Nakajima and E. Sano (NTT)
" Device Technology for InP/InGaAs HBT Lightwave Communication ICs "

[7] Novel Devices , Physics, and Fabrication (Chair, K. Matsumoto, ETL)

The topics covered in this subcommittee are: (1) Single electron devices and their application, theory and experiment, (2) Resonant tunneling devices and their application to circuits, (3) Compound semiconductor devices with new structures, materials, and physics, (4) Other novel devices such as spin devices, quantum computing devices, superconducting devices, etc. Fabrication and characterization of quantum nanostructures for electron devices are also solicited.

Invited Speakers:
O. Astafiev (Univ. of Tokyo)
" Single Far-Infrared Photon Detection Using an SET "
M. Pepper (Univ. of Cambridge)
" Quantised Current in One-Dimensional Channels Induced by Surface Acoustic Waves "
A. Dodabalapur, B. Crone, J.A. Rogers, Z. Bao, Y.Y. Lin, V.R. Raju and H.E. Katz (Bell Labs. Lucent Technol.)
" Organic Transistors for Logic and Flexible Display Applications"

[8] New Materials and Characterization (Chair, S. Zaima, Nagoya Univ.)

Papers are solicited in subject areas including (1) Characterization and processing of group-IV semiconductors, high-/low-k dielectrics, ferroelectrics, and other new materials, (2) Physics and chemistry of surface/interface phenomena, (3) Reliability physics and failure analysis of gate oxides and interconnect systems, and (4) In-situ monitoring and nanometer-scale characterization, but not limited to these subjects.

Invited Speakers:
C. Capasso (Motorola)
" Reliability and Electromigration Failure Modes in Dual Inlaid Cu Interconnects "
A.I. Kingon and J.-P. Maria (North Carolina State Univ.)
" A Comparison of SiO2-Based Alloys as High Permittivity Gate Dielectrics"

Strategic Areas

[9] Low Power Circuits and Devices (Chair, K. Ishibashi, Hitachi)

This subcommittee covers all kinds of architectures, circuits/devices, and design tools (CAD) for low power whether they are elements or LSIs. In addition to new circuit/device ideas, studies on scaled-silicon issues such as low-voltage operation, circuit/device fluctuation, noise, EMI, wiring delay/coupling, clocking, and analog circuits are welcome. Fabricated results are preferable but are not essential.

Invited Speaker:
T. Hiramoto (Univ. of Tokyo)
" Optimum Device Parameters and Scalability of Variable Threshold CMOS (VTCMOS) "

[10] Silicon-on-Insulator Technologies (Chair, M. Yoshimi, Toshiba)

The topics of this session includc (1) SOI Circuit Applications (Low Power/Low Voltage, High Speed, RF, Analog/Linear, etc), (2) Device Manufacturing Issues (Isolation, Silicidation, Plasma Damage, etc), (3) Physics and Modeling of SOI Devices and Circuits (floating-body effect. self-heating, etc), (4) SOI Materials Characterization and Manufacturing, (5) Reliability Issues (Hot Carrier Injection, GOI, Radiation Effects), and so on.

Invited Speakers:
M. Harada (NTT)
" Low-Power RF Circuits on SOI "
H. Mikoshiba, M. Hogyoku, A. Ebina, T. Kadowaki, Y. Sato and M. Yamaguchi (Seiko Epson)
" Low-Power SOI-CMOS Technology and Its Application to Watch-IC "
I. J. Malik (Silicon Genesis)
" TBD "

[11] Non-Volatile Memories (Chair, K. Yoshikawa, Toshiba)

This subcommittee solicits all NV memory (Flash, FeRAM, EPROM, EEPROM, Anti-fuse & others) technology related papers. Topics relating to NV devices include cell device physics & characterization, processing & materials, tunnel dielectrics, ferroelectric materials, reliability, failure analysis, quality assurance & testing, modeling & simulation, integrated circuits, new concept technologies, and new applications & systems (solid state disks, memory cards, programmable logic,---).

Invited Speakers:
K.-M. Chang (Motorola)
" Technology Considerations for High-Speed High-Density Embedded Flash "
J.T. Evans (Radiant Technologies)
" The Role of Ferroelectric Domains in Long Term Reliability "
T. Sakoda (Texas Instruments)
" Hydrogen-Robust Submicron Ir/PZT/Ir Capacitors for Embedded Ferroelectric Memory "

[12] Widegap Semiconductor Materials and Devices (Chair, H. Kawai, Sony)

This topical session will highlight significant advances for wide bandgap semiconductor materials and devices, and will provide a forum for discussions on technological challenges and issues which should be addressed. The materials include III-Nitrides, SiC, ZnO, diamond, and their related alloys. Original papers on growth, characterization, processing, optical and/or electronic devices, and their physics are solicited.

Invited Speakers:
T. Kimoto, H. Yano, N. Miyamoto and H. Matsunami (Kyoto Univ.)
" Recent Progress in SiC MOS and Ion Implantation Technologies for High Power Devices "
M.S. Shur, R. Gaska and A. Khan (Rensselaer Polytechnic Inst)
" Physics of GaN-based Electronic Devices "
M. Kawasaki (Tokyo Inst. of Technol.)
" Can ZnO Eat Market in Optoelectronic Applications? "

[13] Quantum Nanostructures/Devices/Physics (Chair, Y. Arakawa, Univ. of Tokyo)

The scope of this subcommittee covers recent progress in fabrication, physics, and device application of nanostructures, including (1) growth and processing of nanostructures such as quantum wires and dots (2)Transport/optical properties and Tera-Herz/Femto-second dynamics of nanostructures (3) Nano-meter scale characterization such as STM and SNOM (4) electronic devices and optical devices based on quantum phenomena in nanostructures (5) Novel nanostructures related to photonic crystals, magnetic materials, superconductors, insulators, metals, and organic semiconductors.

Invited Speakers:
R.H. Blick (Univ. of Munich)
" Nano-electromechanical Systems and Single Electron Tunneling "
S. Noda (Kyoto Univ.)
" Semiconductor 3D and 2D Photonic Crystals "
Y. Ohno, D.K. Young*, B. Beschoten*, F. Matsukura, H. Ohno and D.D. Awschalom* (Tohoku Univ. and *UC, Santa Barbara)
" Spin-Polarized Current Injection in Ferromagnetic Semiconductor Heterostructures"

[14] Photonic Integration and Packaging (Chair, T. Miya, NTT)

In this strategic subcommittee, papers on photonic integration and packaging technologies from the viewpoint of and/or taking account of system application are solicited in the following areas: (1) Passive PLC (Planar Lightwave Circuit), (2) Hybrid PLC (combination of passive PLC and active devices), (3) Polymer waveguide, (4) LiNbO3, (5) Photonic crystal and (6) Other related devices and technologies.

Invited Speakers:
H. Fujita and H. Toshiyoshi (Univ. of Tokyo)
" MEMS and Optical Applications "
H. Onaka (Fujitsu Labs.)
" Terabit Photonic Networks "

A. Himeno (NTT)
" Silica-Based Planar Lightwave Circuits for the Future Photonic Networks"

[15] System-Level Packaging Technologies (Chair, A. Matsuzawa, Matsushita Electric)

The scope is to bring advanced packaging or module technologies which contribute to the high performance system-level integration. Papers are solicited in the area, but not limited to: high density packaging technologies, total design and CAD technologies including EMI or EMC management, three dimensional integration technologies, micro-process and micro-connection technologies, micro component technologies, high frequency and ultra-high speed packaging and module technologies, module testing technologies, burn-in and KGD (Known Good Die) technologies, and heat sinking technologies.

Invited Speaker:
M. Bonkohara (ASET)
" Current State of Research and Development for Electric System Integration "

REGULAR SESSIONS

Regular Sessions, the major part of the Conference, will include contributed as well as invited papers on all the relevant areas.

SHORT COURSES

Two short courses will be held on August 28, 2000 for young engineers and students. The courses consist of five lectures relating to the following topics. Most lectures are given in Japanese.

Quantum Communication and Quantum Computing in the Internet Era in the 21st Century
Organizer: N. Yokoyama (Fujitsu Labs.)

The arrival of the Internet era has made electronic life and electronic commerce commonplace realities, increasing the demand for even higher degrees of secure communications. As the recent cracking into Japan's governmental offices signifies, the security level of the current internet can be very low. Against this background, quantum encryption and quantum communication have earned increased attention as communication means that ensure complete privacy of communications. The progress of computer technologies facilitated factorization into prime factors. Some experts pointed out that encryption codes, which were regarded as being practically impossible to decipher, might be deciphered at a fraction of the time. In an effort to overcome such problems, research and development activities related to quantum computing are on the increase, mainly in the United States, because quantum computing is recognized as a critically important technology for national defense.

For this tutorial seminar, we have invited five leading researchers in this area to explain the basic theories, to report on the progress of current experiments, and to discuss the future development of these technologies.

1.Mathematical theory for quantum information science
O. Hirota (Tamagawa Univ. Research Inst.)
2. Quantum Teleportation
A. Furusawa (Nikon)
3. Possibility of Quantum Cryptography and Quantum Authentication
K. Nakamura (NEC)
4. Quantum Computation: Concept, algorithm and Decoherence problem
A. Hosoya (Tokyo Inst. of Technol.)
5. Experiments on quantum computers
S. Takeuchi (Hokkaido Univ.)

" Semiconductor Integrated Circuit Technology for Realizing High-Performance Extremely Low-Power Mobile Information Terminals "
Organizer: K. Kotani (Tohoku Univ.)
1. Low Power Integrated Circuit Technologies for High-Performance Extremely Low-Power Mobile Information Terminals
T. Sakurai (Univ. of Tokyo)
2. Low Power LSI Design (Tentative)
K. Torki (CMP, France)
3. RF Analog Circuits and Layout Techniques
T. Tsukahara (NTT)
4. SOI Device Technology for Low-Power LSI Applications
M. Yoshimi (Toshiba)
5. The Non-Volatile Memory Technology and Its Application for Reconfigurable Devices
H. Takasu (Rohm)

RUMP SESSION

Two rump sessions will be held during the conference. The detail of the rump sessions will be announced in the advance

program.

SUBMISSION OF PAPERS

Prospective authors must submit camera-ready papers, two pages in length all figures and tables.

Deadline for receipt of technical papers is April 14, 2000.

Two-page summary must be written in English and typed on 8.5×11 inches or A4-size whited bond paper. The first page must include the title of the paper, author(s), affiliation(s), address, telephone number, fax number, e-mail address, and article text. The second page should be used for indicating figures, tables and photographs. Detailed format information will be available at the conference World Wide Web site. The paper should report original and previously unpublished work, including specific results.

Original 2-page manuscript, 15 copies of printed or photocopied on both sides of a sheet with attached author's application form and copyright form should be sent to SSDM 2000 Secretariat.

Papers to be presented at the conference will be selected mainly by each subcommittee on the basis of content from the submitted paper.

Authors of accepted papers would be notified by mail until the middle of July. All contributors will be requested to give either an oral presentation conforming to a 20-minute format or a poster presentation.

Secretariat of SSDM
c/o Business Center for Academic Societies Japan
5-16-9 Honkomagome, Bunkyo-ku, Tokyo 113-8622, Japan
Phone: ＋81-3-5814-5800 FAX: ＋81-3-5814-5823
E-mail: ssdm@bcasj.or.jp

EXTENDED ABSTRACTS AND PUBLICATION

Accepted papers will be printed without opportunity for further change in the extended abstracts, which will be distributed on the opening day of the conference.
Authors of papers accepted for SSDM 2000 are encouraged to submit the original and significant part of the papers to the Special Issue of the Japanese Journal of Applied Physics. The special issue will be published in 2001.

AGREEMENT NOT TO PRE-PUBLISH ABSTRACTS

Submission of an abstract for review and subsequent acceptance is considered by the committee as an agreement that the work will not be published by the author prior to the presentation at the conference. This policy will be enforced by automatic withdrawal of the paper by the conference committee.

LATE NEWS PAPERS

Late news papers describing important new developments may be submitted. A two-page description must be sent in the camera-ready format as required for the regular papers. The accepted papers will be included in the Extended Abstracts.

Original 2-page manuscript, 15 copies of printed or photocopied on both sides of a sheet with attached author's application form and copyright form should be sent to SSDM 2000 Secretariat.

Deadline for receipt of Late News papers is July 7, 2000.

Notice of acceptance will be mailed by the early in August.

CONFERENCE FORMAT

The conference has been organized to provide as much interaction and discussion among the participants as possible. The program will include a plenary session along with technical sessions comprised of invited and contributed papers for oral or poster presentation.

AWARDS

``SSDM Awards'' will be given to excellent papers presented in the previous conferences.

SSDM Award

for the paper outstandingly contributed to the field of solid state devices and materials, among the papers presented prior to 1999.

SSDM Paper Award
for the best paper presented at the last conference.
SSDM Young Researcher Award
for a few excellent papers by young researchers presented at the last conference.

BANQUET

A buffet dinner will be held on the evening of August 29. Additional tickets (¥6,000 each) may be purchased at the registration desk.

REGISTRATION

Pre-registration is recommended due to the expected large number of participants. In order to pre-register for SSDM 2000, the enclosed Registration Form should be returned with your payment by July 31 to the SSDM 2000 Secretariat. Payment should be made in Japanese yen by bank transfer or bank draft payable to the SSDM 2000 Secretariat. Credit cards are acceptable from overseas attendees only: Diners, Master Card, VISA and AMEX. No personal checks will be accepted. After your remittance has been received, the receipt and a voucher for the participant's kit will be sent by the secretariat early in August.

	Registration Fee (conference)*		Registration Fee (short course)	Banquet
	by July 31	after August 1		
Regular	¥35,000	¥40,000	¥10,000	¥6,000
Student	¥18,000		¥5,000	¥3,000
Accompanying Person				¥3,000

*Includes one ``Extended Abstracts''

Bank transfer to SSDM
A/C No. 075-1229143
Daiichi Kangyo Bank, Hongo Branch, Tokyo
第一勧業銀行　本郷支店(店番号 075) (普) 1229143
口座名：国際固体素子・材料コンファレンス

CANCELLATION

Conference:
In case of cancellation, a fee of ¥3,000 will be deducted from the refund before August 10. Cancellations should be made in writing to the SSDM 2000 Secretariat.
No cancellation will be allowed after August 11.
Extended Abstracts will be sent to absent registrants after the conference.

Short Course:
In case of cancellation, a fee of ¥2,000 will be deducted from the refund before August 10. Cancellations should be made in writing to the SSDM 2000 Secretariat.
No cancellation will be allowed after August 11.

FINANCIAL SUPPORT

Limited financial support for presentations by students and by researchers from newly industrializing countries is available. People who are interested in the support should directly contact to the Steering Committee, c/o Business Center for Academic Societies Japan, e-mail:ssdm@bcasj.or.jp.

VISA REQUIREMENT

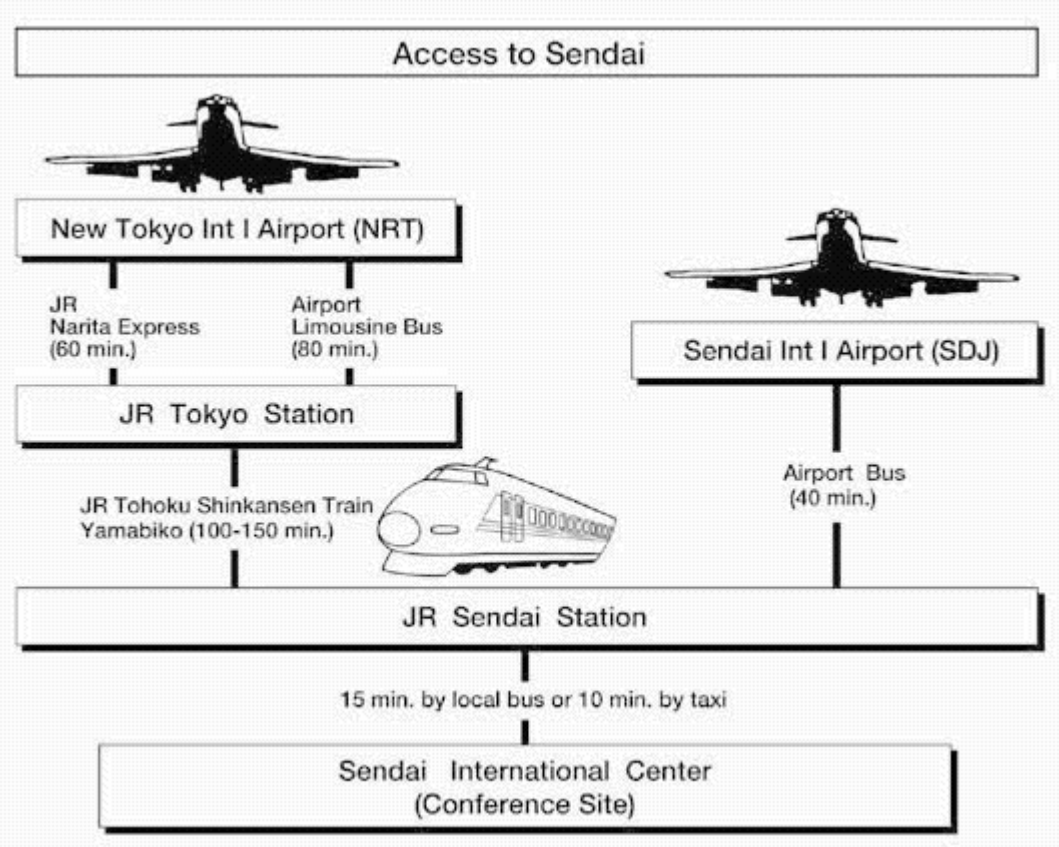
All foreign participants must have valid passport. Participants from countries where a visa is required to enter Japan are recommended to apply at the nearest Japanese embassy in their countries as soon as possible.

LOCATION

Sendai is located to the Pacific Ocean side at 300 km north of Tokyo. It takes about 2 hours from Tokyo by Tohoku-Shinkansen(bullet train) and 1 or 2 hours from most other cities in Japan by air.

Sendai was built as a castle town in 1600 and continues to develop as the center of politics, economy and culture in the Northeast Region of Japan, and is called “academic city” as a center of education. There are many scenic spots and places of historical interest in and around Sendai, such as Matsushima, one of the most beautiful places in Japan. There are also many famous hot spring resorts near Sendai.

In more details, see ①http://www.city.sendai.jp/ ②http://www.jnto.go.jp/05regional/miyagi/



OFFICIAL TRAVEL AGENT

Japan Travel Bureau(JTB) has been appointed as the official travel agent for the Conference and will handle hotel accommodations.

Japan Travel Bureau(JTB)
Tohoku Communications Inc.
Kotsukosha Bldg 3F, 3-6-8 Chuo,
Aoba-ku, Sendai 980-0021, Japan
Phone: +81-22-262-5055
FAX: +81-22-262-5002
E-mail: tcs02@thk.jtb.co.jp

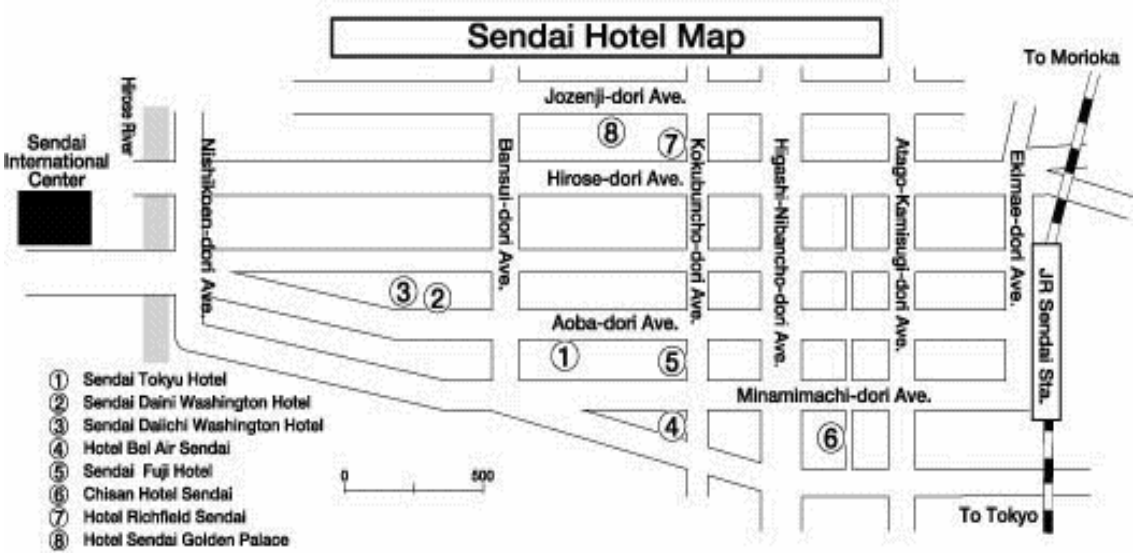
HOTEL ACCOMMODATIONS

The Organizing Committee of SSDM 2000 has a block of sufficient rooms at discount convention rates to accommodate participants and accompanying persons. The Accommodation Reservation Form should be sent by postal mail or fax to Japan Travel Bureau, Inc. (JTB) before July 19. If a room at your first choice hotel is unavailable, the second choice (or third choice) hotel will be assigned. Reservation confirmation will be sent to you by E-mail or by fax.

No	Hotels	Single	Twin	From the Conference site
1	Sendai Tokyu Hotel	9,500 JPY	16,000 JPY	15 min on foot
2	Sendai Daini Washington Hotel	8,700 JPY	15,400 JPY	10 min on foot
3	Sendai Daiichi Washington Hotel	7,700 JPY	Not available	10 min on foot
4	Hotel Bel Air Sendai	8,000JPY	15,000JPY	20 min on foot
5	Sendai Fuji Hotel	7,350JPY	12,600JPY	20 min on foot
6	Chisan Hotel Sendai	7,600JPY	13,600JPY	30 min on foot
7	Hotel Richfield Sendai	6,825JPY	14,806JPY	20 min on foot
8	Hotel Sendai Golden Palace	6,800JPY	13,600JPY	25 min on foot

*The amount of charges is per room for one night.
*Above room rate includes government tax and service charge but no meal.

*Please pay all charges directly to the hotel in cash or by credit card when checking out.
*Inform JTB of any changes in your dates of arrival and/or departure or of cancellation.
*You MUST give notice to JTB if you intend to check in at the hotel later than 21:00 on the intended arrival date, or your reservation may be canceled.



GENERAL INFORMATION

PASSPORT AND VISA

Every foreign visitor entering Japan must have a valid passport. Visitors from countries whose citizens must have visas should apply to a Japanese consular office or diplomatic mission in their respective country.
For further details, please contact your travel agent or the local consular office in your country.

CUSTOMS

Japanese customs is fairly lenient and allows bringing in items necessary for personal use. Duty-free imports are; 3 bottles of liquor; 400 cigarettes or 100 cigars; 2 ounces of perfume; gifts and souvenirs other than the above whose total market value does not exceed ¥200,000.Strictly prohibited are firearms and other types of weapons, and narcotics.

INSURANCE

The organizer cannot accept responsibility for accidents, which might occur. Delegates are encouraged to obtain travel insurance (medical, personal accident, and luggage) in their home country prior to departure.

CLIMATE

The temperature in Sendai during the period of the Conference ranges between 21C and 28C.

CURRENCY EXCHANGE

Only Japanese Yen is acceptable at regular stores and restaurants. Certain foreign currencies and credit cards may be accepted at a limited number of hotels, restaurants and souvenir shops. You can buy at foreign exchange banks and other authorized money exchangers on presentation of your passport.

TRAVELER'S CHECKS AND CREDIT CARDS

Traveler's checks are accepted only by leading banks and major hotels in principal cities, and the use of traveler's checks in Japan is not as popular as in some other countries. VISA, MasterCard, Diners Club, and American Express are widely accepted at hotels, department stores, shops, restaurants and nightclubs.

TIPPING

In Japan, tips are not necessary anywhere, even at hotels and restaurants.

ELECTRICAL APPLIANCES

Japan operates on 100 volts for electrical appliances. The frequency is 50 Hz in eastern Japan including Sendai and 60 Hz in western Japan including Kyoto and Osaka.

SHOPPING

The business hours of most department stores are open from 10:00 to 19:00. They are open on Sundays and national holidays, but close on Monday, Wednesday or Thursday. Business hours for retail shops differ from each other, most operate from 10:00 to 20:00, and are open on Sundays and national holidays.

ORGANIZING COMMITTEE

Chairperson: T. Ohmi *(Tohoku Univ.)*

Vicechairperson: Y. Horiike *(Univ. of Tokyo)*

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C. Hamaguchi *(Osaka Univ.)*
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T. Ikoma *(Texas Instruments Japan)*
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H. Ishikawa *(Fujitsu Labs.)*
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K. Natori *(Univ. of Tsukuba)*
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K. Ohta *(Sharp)*
T. Okabe *(SIRIJ)*
K. Okumura *(Toshiba)*
T. Sakamoto *(ETL)*
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M. Hirayama (Tohoku Univ.)

Local Arrangement: K. Kotani (Tohoku Univ.)
H. Nakase (Tohoku Univ.)

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Vice chairperson	A. Matsuzawa *(Matsushita Electronics)*
	N. Yokoyama *(Fujitsu Labs.)*
Secretary:	T. Kondo *(Univ. of Tokyo)*

Subcommittee Members:

[1] Advanced Silicon Circuits and Systems

Chair:	T. Shibata *(Univ. of Tokyo)*
Members:	T. Aoki *(Tohoku Univ.)*
	M. Ikeda *(Univ. of Tokyo)*
	T. Morie *(Hiroshima Univ.)*
	M. Yamashina *(NEC)*

[2] Advanced Silicon Devices and Device Physics

Chair:	S. Kawamura *(Fujitsu)*
Members:	S. Deleonibus *(LETI)*
	D. Hisamoto *(Hitachi)*
	K. Ishimaru *(Toshiba)*
	T. Kuroi *(Mitsubishi Electric)*
	S. Odanaka *(Matsushita Electronics)*
	N. Sano *(Univ. of Tsukuba)*
	K. Takeuchi *(NEC)*

[3] Silicon Process / Materials Technologies

Chair:	T. Kikkawa *(Hiroshima Univ.)*
Members:	Y. Furumura *(Fujitsu Labs.)*
	T. Hattori *(Sony)*
	H. Katsuhiko *(Toshiba)*
	M. Hori *(Nagoya Univ.)*
	N. Kobayashi *(Hitachi)*
	M. Okuyama *(Osaka Univ.)*
	S. Saito *(NEC)*
	M. Sekine *(ASET)*
	K. Yamabe *(Univ. of Tsukuba)*

[4] High-Speed/High-Frequency Devices and Circuits

Chair:	K. Honjo *(NEC)*
Members:	Y. Itoh *(Mitsubishi Electric)*
	K. Joshin *(Fujitsu Labs.)*
	H. Kondo *(Hitachi)*
	M. Muraguchi *(NTT Elec.)*
	D. Pavlidis *(Solid State Electronics Lab.)*
	S. Watanabe *(Toshiba)*

[5] Optoelectronic Devices

Chair:	H. Ishikawa *(Fujitsu Labs.)*
Members:	H. Sugo *(NEC)*
	S. Tanaka *(Hitachi)*
	Y. Tohmori *(NTT)*
	H. Wada *(Oki Electric)*
	W. Wei *(Chinese Academy Sci.)*

[6] Compound Semiconductor Materials and Device Processes

Chair:	K. Horikoshi *(Waseda Univ.)*
Members:	K. Ando *(Tottori Univ.)*
	K. Imanishi *(Fujitsu Labs.)*
	T. Ishibashi *(NTT)*

T. Oka *(Hitachi)*
T. Okumura *(Tokyo Metropolitan Univ.)*
K. Ploog *(Forschungsverbund Berlin e. V)*

[7] Novel Devices , Physics, and Fabrication

Chair: K. Matsumoto *(ETL)*

Members: H. Ahmed *(Cambridge Univ.)*
S.Y. Chou *(Princeton Univ.)*
N. Horiguchi *(Fujitsu Labs.)*
K. Maezawa *(Nagoya Univ.)*
A. Toriumi *(Toshiba)*
J.-S. Tsai *(NEC)*

[8] New Materials and Characterization

Chair: S. Zaima *(Nagoya Univ.)*

Members: T. Fuyuki *(Nara Inst. Sci. & Technol.)*
H. Kawasaki *(Motorola)*
M. Miyao *(Kyushu Univ.)*
S. Miyazaki *(Hiroshima Univ.)*
K. Nikawa *(NEC)*
S. Takagi *(Toshiba)*
E. Tokumitsu *(Tokyo Inst. of Technol.)*

[9] Low Power Circuits and Devices

Chair: K. Ishibashi *(Hitachi)*

Members: S. Kawahito *(Shizuoka Univ.)*
S. Kawashima*(Fujitsu Labs.)*
T. Kuroda *(Toshiba)*
H. Makino *(Mitsubishi Electric)*

[10] Silicon-on-Insulator Technologies

Chair: M. Yoshimi *(Toshiba)*

Members: T. Ipposhi *(Mitsubishi Electric)*
Y. Kado *(NTT)*
K. Mitani *(Shinetsu Electronics)*
T. Sugii *(Fujitsu Labs.)*
T. Tsuchiya *(Shimane Univ.)*

[11] Non-Volatile Memories

Chair: K. Yoshikawa *(Toshiba)*

Members: Y. Arimoto *(Fujitsu Labs.)*
T. Kobayashi *(Hitachi)*
T. Nakamura *(Rohm)*
T. Okazawa *(NEC)*
T. Otsuki *(Matsushita Electronics)*

[12] Widegap Semiconductor Materials and Devices

Chair: H. Kawai *(Sony)*

Members: H. Amano *(Meijo Univ.)*
S. Chichibu *(Univ. of Tsukuba)*
Y. Koide *(Kyoto Univ.)*
Y. Ohno *(NEC)*
H. Okumura *(ETL)*
A. Suzuki *(Sharp)*

[13] Quantum Nanostructures/Devices/Physics

Chair: Y. Arakawa *(Univ. of Tokyo)*

Members:	K. Asakawa *(FESTA)*
	K. Hirakawa *(Univ. of Tokyo)*
	Y. Hirayama *(NTT)*
	K. Nakamura *(NEC)*
	M. Sugawara *(Fujitsu)*
	K. Tsutsui *(Tokyo Inst. Technol.)*

[14] Photonic Integration and Packaging

Chair:	T. Miya *(NTT)*
Members:	M. Fujiwara *(NEC)*
	H. Miyazawa *(Furukawa Electric)*
	K. Tanaka *(Fujitsu)*
	H. Uetsuka *(Hitachi Cable.)*

[15] System-Level Packaging Technologies

Chair:	A. Matsuzawa *(Matsushita Electronics)*
Members:	Y. Kohara *(Oki Electric)*
	M. Minamizawa *(Fujitsu)*
	K. Ohtsuka *(Meisei Univ.)*
	T. Sudo *(Toshiba)*